


Substitute for Form 1449/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(use as many sheets as necessary)**
Complete if Known

Application Number	10/082,997			
Filing Date	February 25, 2002			
First Named Inventor:	Steven N. Towle			
Art Unit	1753			
Examiner Name	McDonald, Rodney Glenn			
Sheet	1	of 1	Attorney Docket Number	42390P5783D

NON PATENT LITERATURE DOCUMENTS

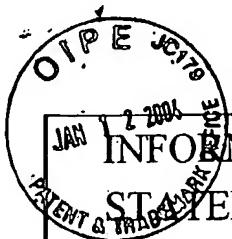
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
<i>JH</i>		ANNEN, A., ET AL., Erosion of amorphous hydrogenated boron-carbon thin films, Journal of Nuclear Materials 231 (1996) pgs. 151-154, © 1996 Elsevier Science, B.V.	
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by helicon plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (20) 13 May 1996, pgs. 2864-2866, © American Institute of Physics.	
		ENDO, KAZUHIKO, ET AL., Fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, J. Appl. Phys. 78 (2), 15 July 1995, pgs. 1370-1372, © 1995 American Institute of Physics.	
		ENDO, KAZUHIKO, ET AL., Nitrogen doped fluorinated amorphous carbon thin films grown by plasma enhanced chemical vapor deposition for low dielectric constant interlayer dielectrics, Appl. Phys. Lett. 68 (25), 17 June 1996, pgs. 3656-3658 © 1996 American Institute of Physics.	
		MATSUBARA, Y., ET AL., Low-k Fluorinated Amorphous Carbon Interlayer Technology for Quarter Micron Devices, ULSI Device Development Labs, *Microelectronic Res. Labs., **VLSI Manufacturing Engineering Division, NEC Corporation, 1120 Shimokuzawa, Sagamihara, Kanagawa, 229, Japan, 4 pages, No Date.	
		SHARPOV, V.M., ET AL., Erosion of a-B/C : H films under deuterium plasma irradiation, Journal of Nuclear Materials 220-222 (1995) 930-933, pgs. 930-933, © 1995 Elsevier Science B.V.	
<i>Mr</i>		YAMAKI, T., ET AL., Thermal desorption spectroscopy of boron/carbon films after keV deuterium irradiation, Journal of Nuclear Materials 217 (1994) 154-160, pgs. 154-160, © 1994 Elsevier Science B.V.	

Examiner Signature	<i>Rodney Glenn</i>	Date Considered	<i>3/3/04</i>
--------------------	---------------------	-----------------	---------------

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.



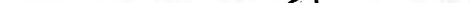
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

 INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number 10/082,997	
		Filing Date February 25, 2002	
		First Named Inventor: Steven N. Towle	
		Art Unit 1753	
		Examiner Name McDonald, Rodney Glenn	
Sheet	1	of 1	
Attorney Docket Number 42390P5783D			

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		SAH, R.E., Mass Spectrometric Study Of Gas Evolution From Plasma-Deposited Fluorohydrogenated Amorphous Carbon Films On Heating, Thin Solid Films, International Journal on the Science and Technology of Thin and Thick Films, 167, December 15 th , 1988, pgs. 255-260, © Elsevier Sequoia/Printed in The Netherlands.	
		WINTER, J., A comparison of tokamak operation with metallic getters (Ti, Cr, Be) and boronization, Journal of Nuclear Materials, Volumes 176 & 177, December 1990, pgs. 14-31, © Elsevier Science Publishers B.V. (North Holland).	

Examiner Signature		Date Considered	3/3/04
-----------------------	---	-----------------	--------

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English Translation is attached.
This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SENT FEES OR COMPLETED FORMS TO THIS ADDRESS.
SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.